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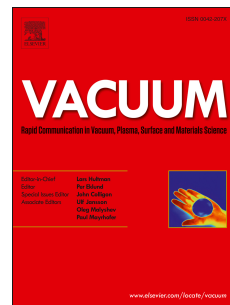
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Features of microstructure of ZrN, Si₃N₄ and ZrN/SiN_x nanoscale films irradiated by Xe ions

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Abstract

The article reports on the TEM investigations of microstructure features after Xe irradiation (360 keV and $5 \cdot 10^{16} \text{ cm}^{-2}$) of ZrN, Si₃N₄ monolithic films and ZrN/SiN_x multilayered film deposited by magnetron sputtering. Results of TEM study of ZrN nanocrystalline film, irradiated by Xe ions, have shown that this film seems to be almost unaffected by the implantation. Only a small amount of damage is observed. In SiN_x

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